Product data sheet

1. General description

Ultrafast power diode in a SMC package.

2. Features and benefits

- Fast switching
- SMC package
- · High voltage capability
- Low forward voltage drop
- Low leakage current
- Low thermal resistance
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- · High frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit	
Absolute	Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage		600			V		
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; $T_{lead} \le 96$ °C; Fig. 1; Fig. 2; Fig. 3	5			А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 μ s; $T_{lead} \le 96$ °C; square-wave pulse	10			А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	130			А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	143		А			
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit		
Static ch	Static characteristics							
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.10	1.35	V	
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>		-	0.9	1.15	V	
Dynamic characteristics								
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 50 \text{ A}/\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	45	-	ns	

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	K	cathode		K — A 001aaa020			
2	Α	anode	1 2	oo raaa020			

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
MUR560	SMC	Hermetically sealed plastic package; SMC; 2 leads	SMC		

7. Marking

Table 4. Marking codes

Type number	Marking codes
MUR560	560

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; square-wave pulse; $T_{lead} \le 96$ °C; Fig. 1; Fig. 2; Fig. 3	5	А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{lead} \le 96 °C$; square-wave pulse	10	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	130	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse;	143	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C

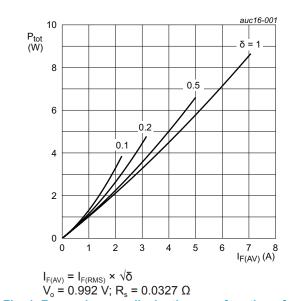
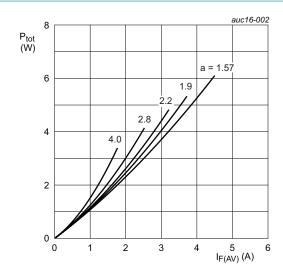


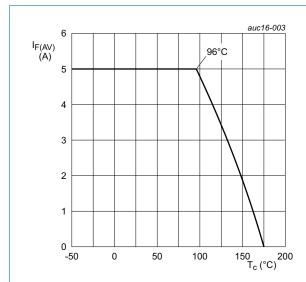
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ Vo = 0.992 V; Rs = 0.0327 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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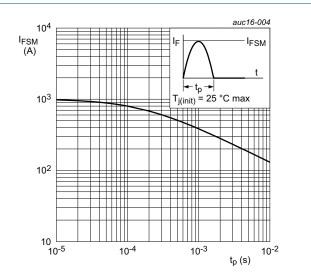


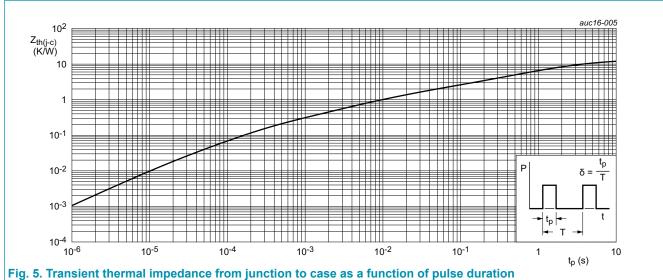
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Ultrafast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-c)}	thermal resistance from junction to case	mounted on a minimum footprint printed-circuit board (FR4); Fig. 5		-	-	12	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	n to printed-circuit board (FR4)		-	75	-	K/W

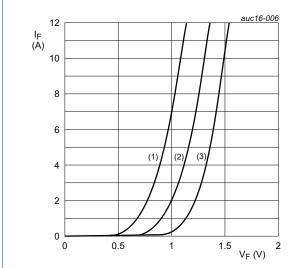


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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static characteristics							
V _F forward current		I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.10	1.35	V	
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.9	1.15	V	
I _R	reverse current	V _R = 600 V; T _j = 25 °C		-	3	μA	
		V _R = 600 V; T _j = 150 °C	-	-	250	μA	
Dynamic	characteristics		,			'	
Q_r	reverse charge	$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	216	-	nC	
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	420	-	nC	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	45	-	ns	
		$I_F = 0.5 \text{ A}$; $I_R = 1 \text{ A}$; $I_{R(meas)} = 0.25 \text{ A}$; $T_j = 25 ^{\circ}\text{C}$; Step recovery	-	-	65	ns	
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	64	-	ns	
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	88	-	ns	
I _{RM}	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	6.7	-	А	
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	9.5	-	А	
E _{as}	non-repetitive avalanche energy			-	-	mJ	



 $V_o = 0.992 \text{ V}; R_s = 0.0327 \Omega$

(1) $T_i = 150 \,^{\circ}\text{C}$; typical values

(2) T_i = 150 °C; maximum values

(3) $T_j = 25$ °C; maximum values



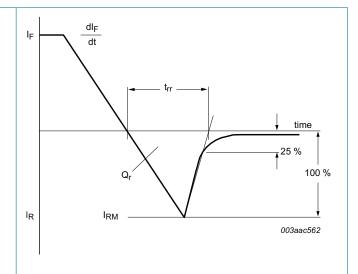
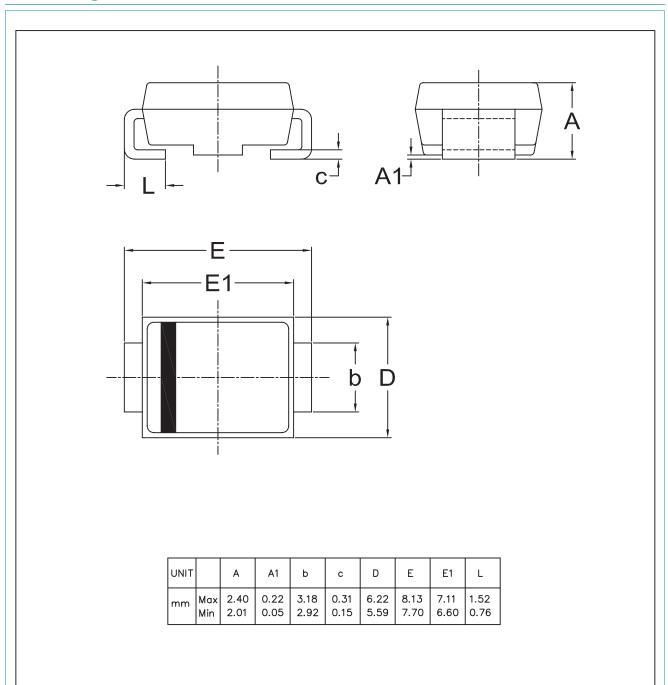


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Remark: Dimensions D and E1 do not include mold flash.

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product Production [short] data sheet		This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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